

IN THE SPECIFICATION

Please delete paragraph [0004] and replace it with the following:

--[0004] Certain ICs ~~devices~~ in telecommunications applications comprise a structure as known as “T-gates.” T-gates are typically required to have gate sizes less than 0.4 μm . GaAs FET performance depends on the gate width which is the short dimension of the gate structure. As the gate length is reduced, gate resistance increases due to the reduced cross-sectional gate area. This increased resistance adversely effects device performance. --

Please delete paragraph [0009] and replace it with the following:

-- [0009] The principles of the present invention, as embodied and broadly described herein, provide a method of fabricating T-gates using optical lithography. In one embodiment, the present invention provides a device manufacturing method comprises XXX comprising: (i) providing a substrate; (ii) providing a first layer of electromagnetic radiation sensitive material on said substrate; (iii) providing a second layer of electromagnetic radiation sensitive material on said first layer of radiation sensitive material, said second layer of radiation sensitive material being of a different material than said first layer of radiation sensitive material; (iv) providing a beam of electromagnetic radiation using an illumination system; (v) imparting said beam of radiation with a desired pattern in its cross-section by employing a patterning device; and (vi) projecting said patterned beam of radiation onto a target portion of said first and second layers of radiation sensitive material. --